

DOSEMI

SiC MOSFET

DM800S12TDRB

1200V/80mΩ SiC Mosfet without Diode

General Description

DOSEMI MOSFET Power Discrete provides ultra low conduction loss as well as low switching loss. They are designed for the applications such as hybrid and electric vehicle.

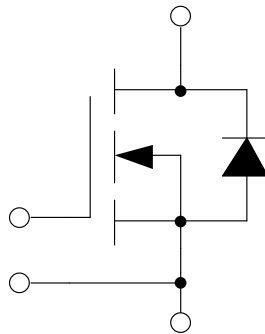
Features

- SiC power MOSFET
- Low $R_{DS(on)}$
- Low inductance case avoid oscillations
- ROHS

Typical Applications

- Automotive application
- Hybrid and electric vehicle
- Inverter for motor drive

Equivalent Circuit Schematic



Type	Package	Marking	Shipping
DM800S12TDRB	TO-247PLUS-4L	DM800S12TDRB	30Units/Tube

Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**Mosfet**

Symbol	Description	Value	Unit
V_{DSS}	Drain-Source Voltage	1200	V
V_{GSSmax}	Gate-Source Voltage	-8/+22	V
V_{GSSop}	Gate-Source Voltage	-4/+15	V
I_D	Drain Current @ $T_{vj}=175^{\circ}\text{C}$	37	A
P_D	Maximum Power Dissipation @ $T_{vj}=175^{\circ}\text{C}$	162	W

Body Diode

Symbol	Description	Value	Unit
I_F	Source Current @ $T_{vj}=175^{\circ}\text{C}$	30	A

Discrete

Symbol	Description	Values	Unit
T_{vjop}	Operating Junction Temperature	-40 to +175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$
T_S	Soldering Temperature, 1.6mm from case for 10s	260	$^{\circ}\text{C}$

Mosfet Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$I_D=20\text{A}, V_{GS}=15\text{V}, T_{vj}=25^\circ\text{C}$		80.0		m Ω	
		$I_D=20\text{A}, V_{GS}=15\text{V}, T_{vj}=150^\circ\text{C}$		98.7			
		$I_D=20\text{A}, V_{GS}=15\text{V}, T_{vj}=175^\circ\text{C}$		105			
$V_{GS(th)}$	Gate-Source Threshold Voltage	$I_D=5.0\text{mA}, V_{DS}=V_{GS}, T_{vj}=25^\circ\text{C}$		2.8		V	
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=V_{DSS}, V_{GS}=0\text{V}, T_{vj}=25^\circ\text{C}$			100	μA	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=V_{GSS}, V_{DS}=0\text{V}, T_{vj}=25^\circ\text{C}$			200	nA	
R_{Gint}	Internal Gate Resistance			3.3		Ω	
C_{iss}	Input Capacitance			1.67		nF	
C_{oss}	Output Capacitance	$V_{GS}=0\text{V}, V_{DS}=800\text{V}, f=100\text{kHz}$		67.4		pF	
C_{rss}	Reverse Transfer Capacitance			4.38		pF	
Q_g	Total Gate Charge	$I_D=18\text{A}, V_{DS}=800\text{V}, V_{GS}=-4/+15\text{V}$		36.0		nC	
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=800\text{V}, I_D=20\text{A}, R_{Gon}=10\Omega, R_{Goff}=5.6\Omega, V_{GS}=-4/+15\text{V}, L_S=40\text{nH}, T_{vj}=25^\circ\text{C}$		6		ns	
t_r	Rise Time			10		ns	
$t_{d(off)}$	Turn-Off Delay Time			12		ns	
t_f	Fall Time			39		ns	
E_{on}	Turn-On Switching Loss			0.65		mJ	
E_{off}	Turn-Off Switching Loss			0.09		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{DS}=800\text{V}, I_D=20\text{A}, R_{Gon}=10\Omega, R_{Goff}=5.6\Omega, V_{GS}=-4/+15\text{V}, L_S=40\text{nH}, T_{vj}=150^\circ\text{C}$		6		ns
t_r	Rise Time				10		ns
$t_{d(off)}$	Turn-Off Delay Time				13		ns
t_f	Fall Time				39		ns
E_{on}	Turn-On Switching Loss			0.71		mJ	
E_{off}	Turn-Off Switching Loss			0.09		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=800\text{V}, I_D=20\text{A}, R_{Gon}=10\Omega, R_{Goff}=5.6\Omega, V_{GS}=-4/+15\text{V}, L_S=40\text{nH}, T_{vj}=175^\circ\text{C}$			6		ns
t_r	Rise Time				10		ns
$t_{d(off)}$	Turn-Off Delay Time				13		ns
t_f	Fall Time				39		ns
E_{on}	Turn-On Switching Loss			0.72		mJ	
E_{off}	Turn-Off Switching Loss			0.09		mJ	

Body Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage	$I_S=10\text{A}, V_{GS}=-4\text{V}, T_{vj}=25^\circ\text{C}$		4.65		V
		$I_S=10\text{A}, V_{GS}=-4\text{V}, T_{vj}=175^\circ\text{C}$		4.10		

Discrete Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per Mosfet)		0.843	0.927	K/W

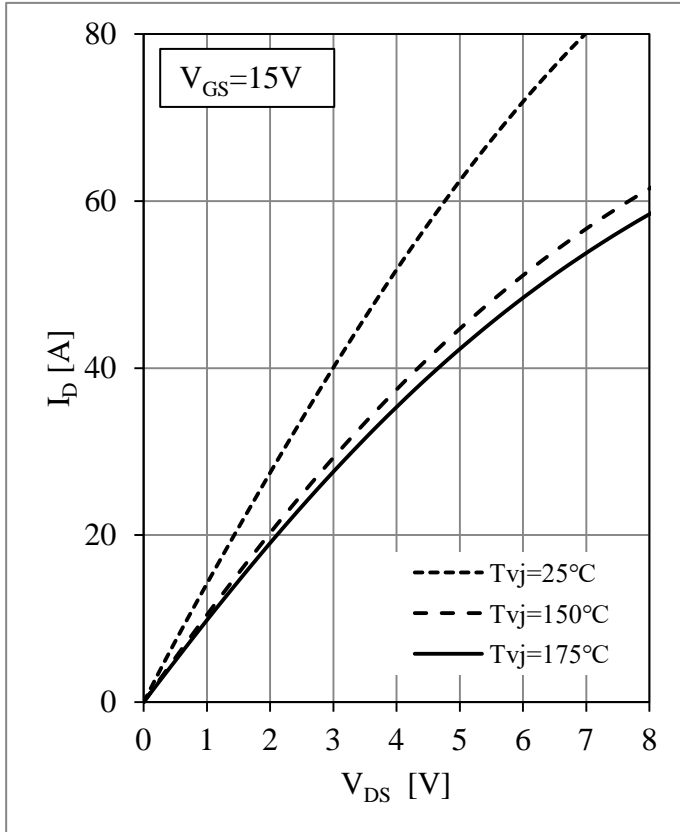


Fig 1. MOSFET Output Characteristics

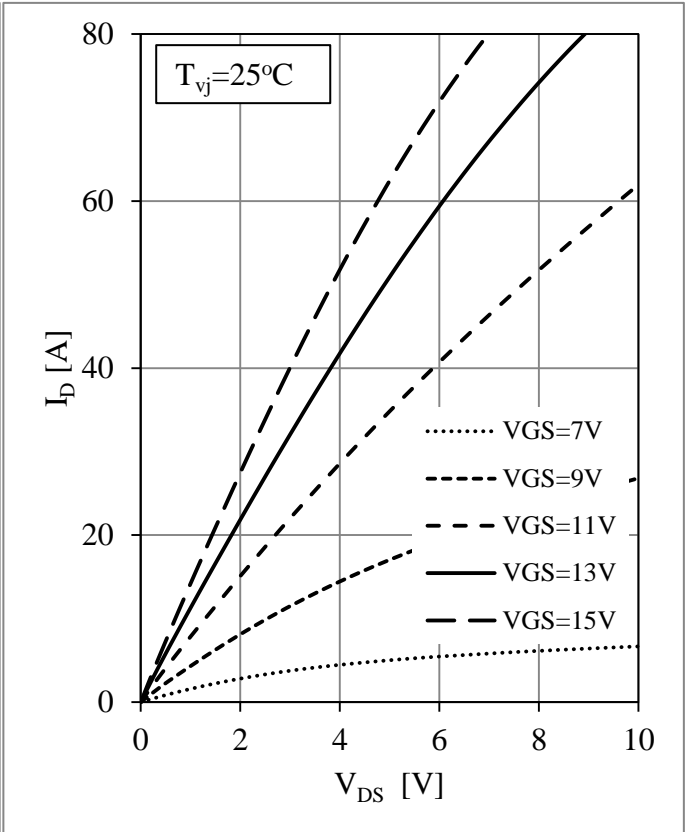


Fig 2. MOSFET Output Characteristics

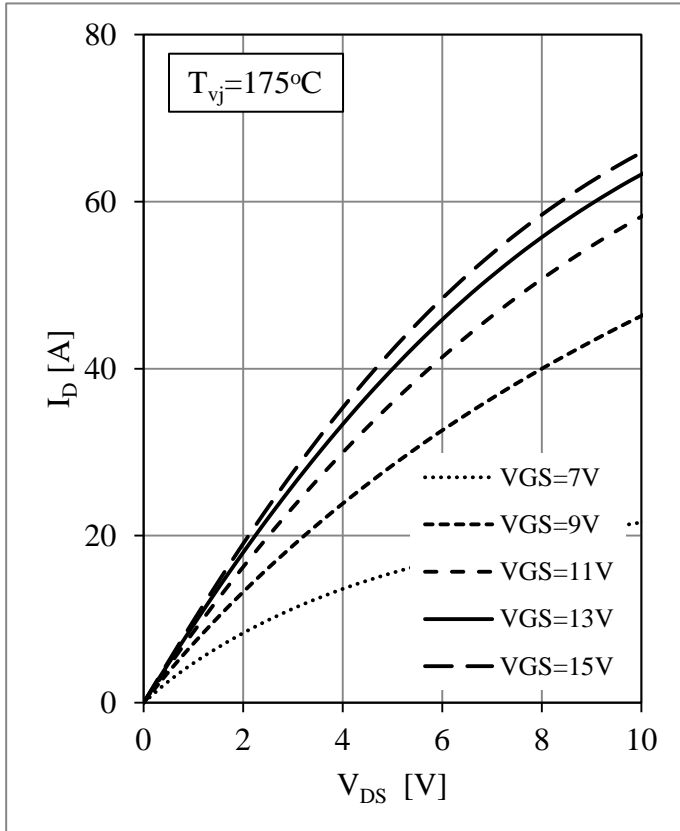


Fig 3. MOSFET Output Characteristics

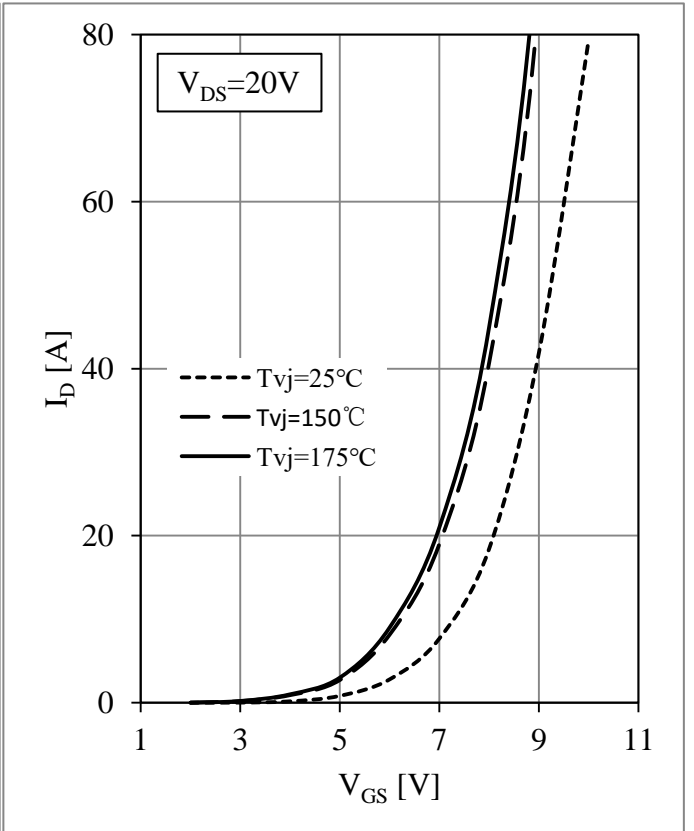


Fig 4. MOSFET Transfer Characteristics

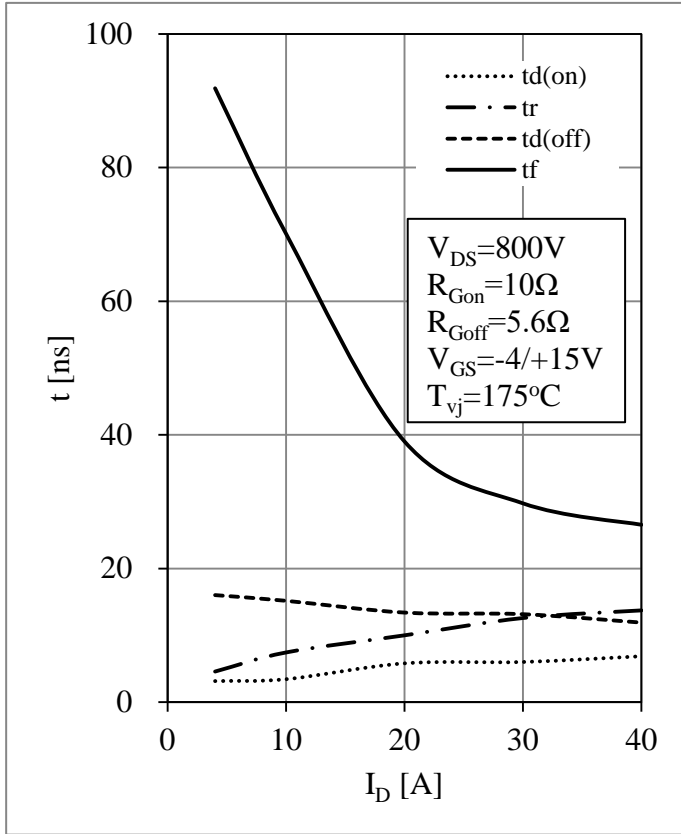


Fig 5. MOSFET Switching Times as. I_D

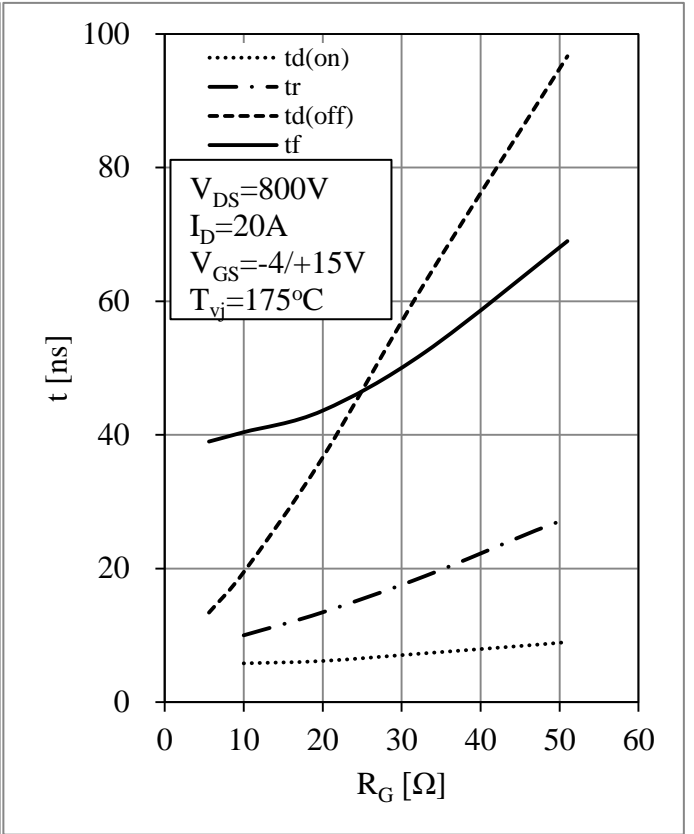


Fig 6. MOSFET Switching Times as. R_G

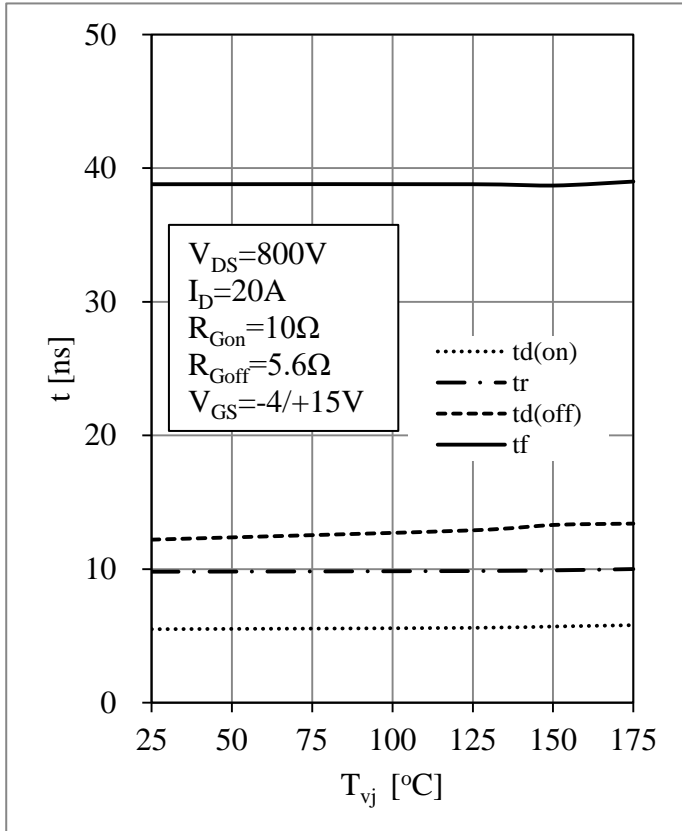


Fig 7. MOSFET Switching Times vs. T_{vj}

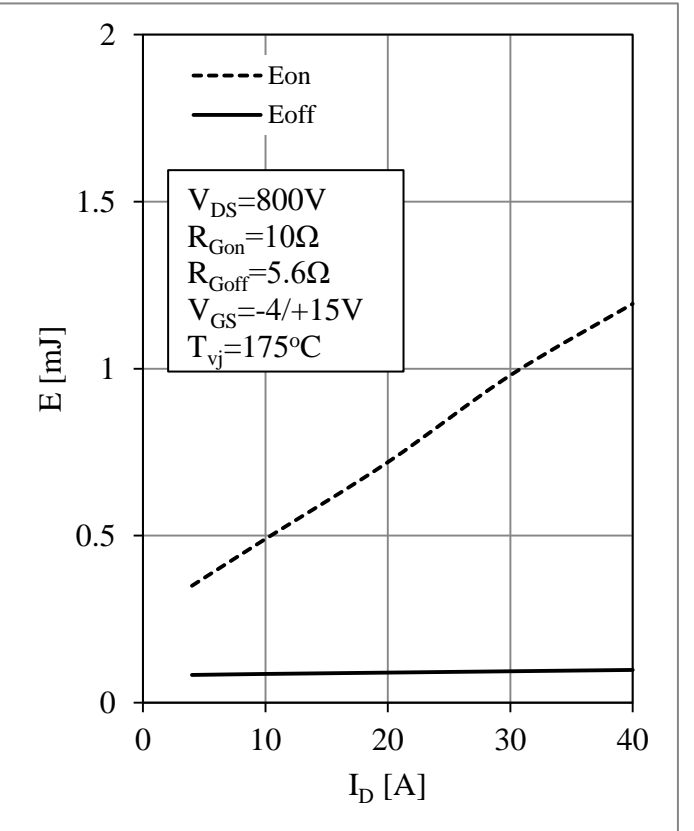


Fig 8. Switching Energy Loss vs. I_D

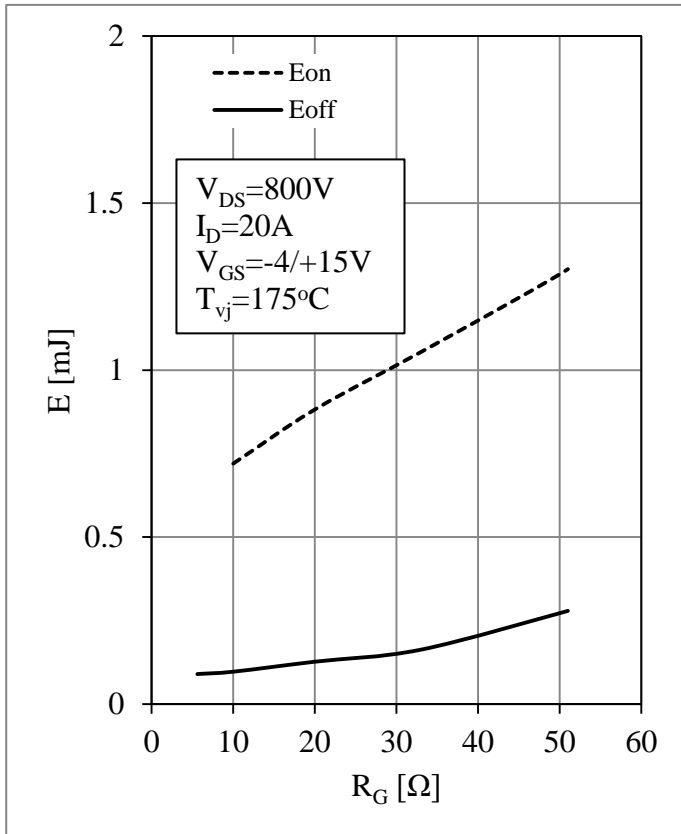


Fig 9. Switching Energy Loss vs. R_G

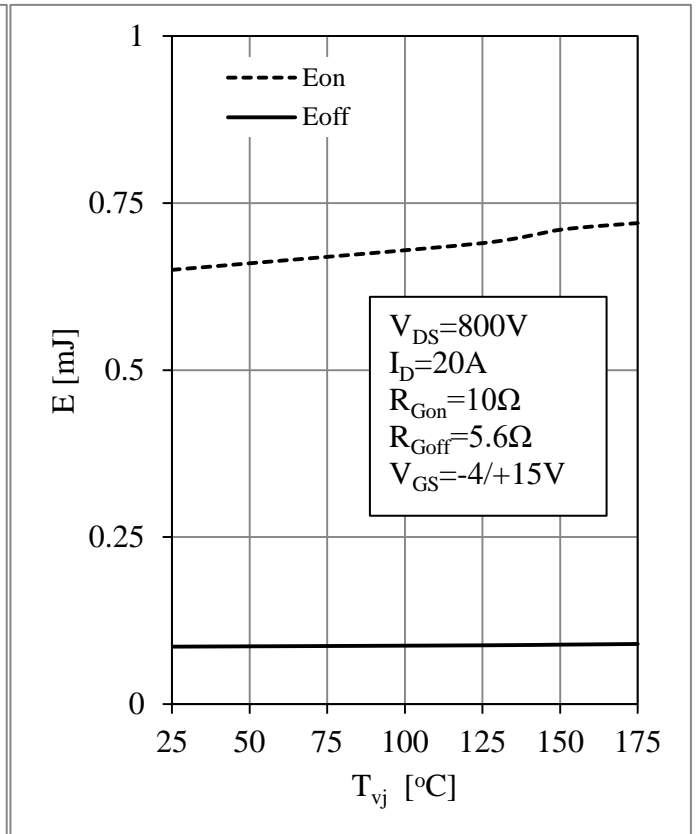


Fig 10. Switching Energy Loss vs. T_{vj}

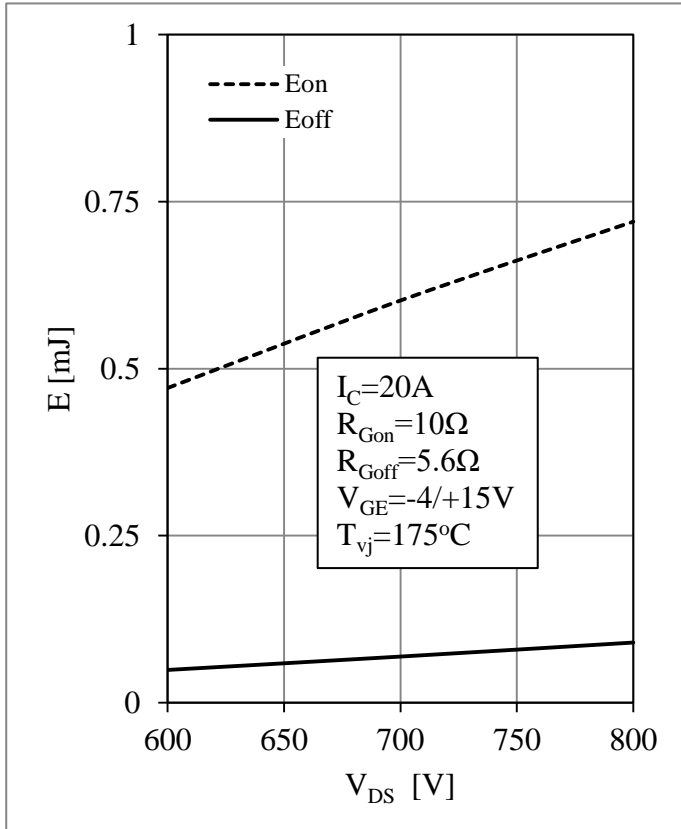


Fig 11. Switching Energy Loss vs. V_{DS}

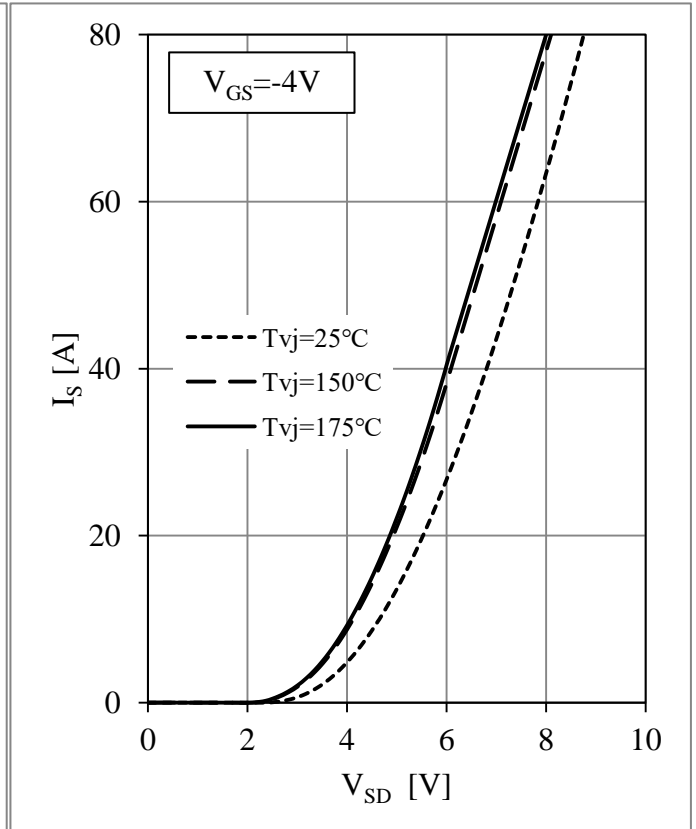


Fig 12. Body Diode Characteristics

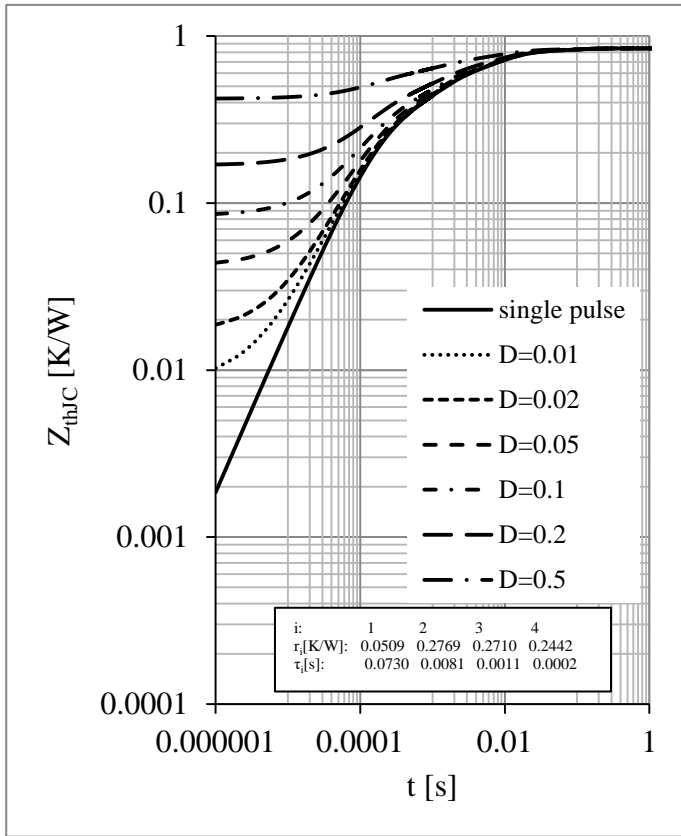
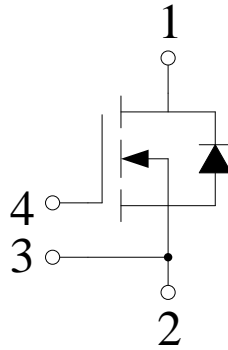


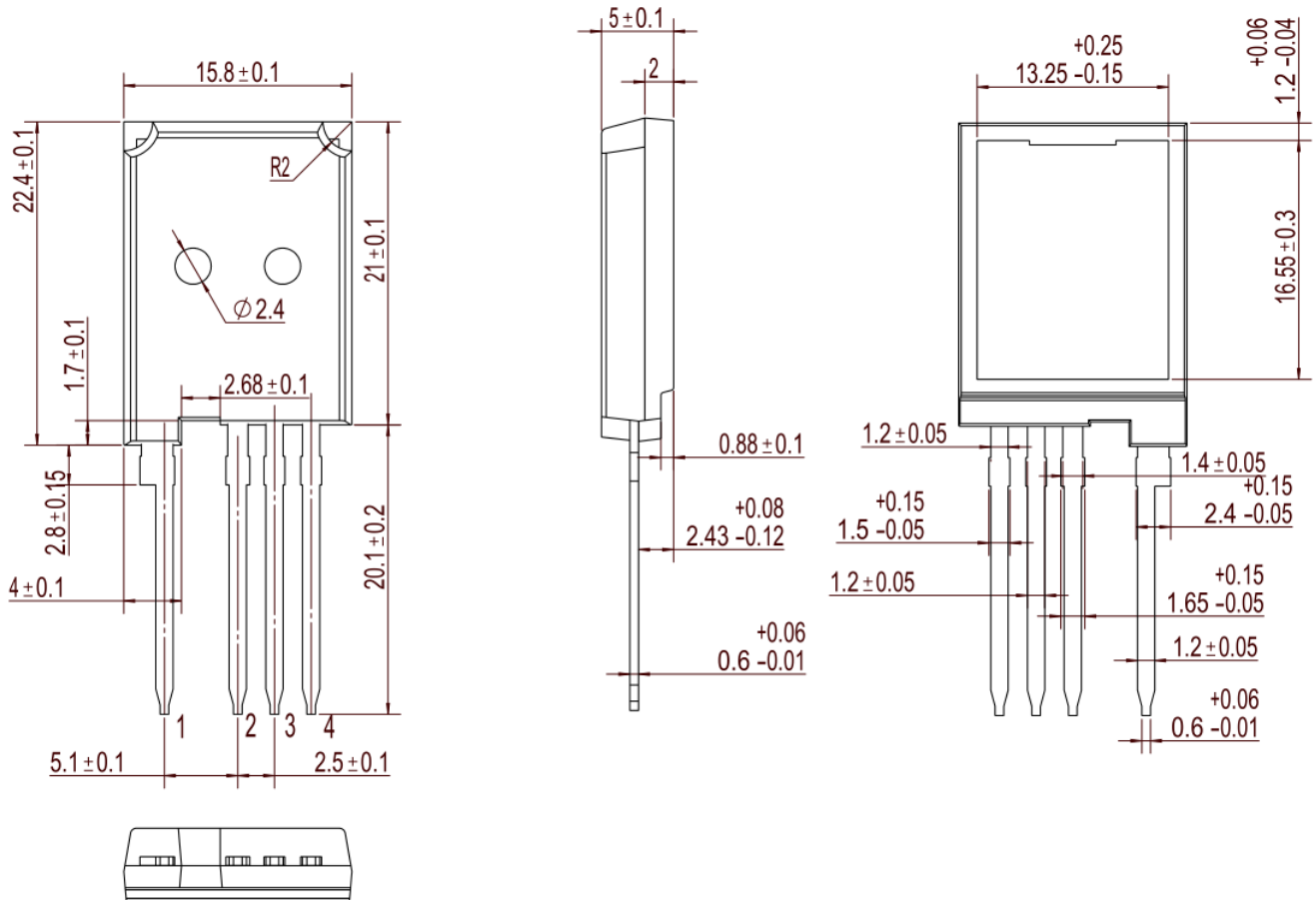
Fig 13. MOSFET Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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